

HF/UHF SMD TCVCXO**Ultra Low Phase Noise**

7 Pad 25x22x7mm SMD

Description: The CTXW Series of SMD temperature compensated, voltage controlled crystal oscillators (TCVCXO), provides High and Ultra High Frequency with excellent temperature stability, extremely low phase noise and jitter with a variety of different output types in a small surface mount FR4 based package.

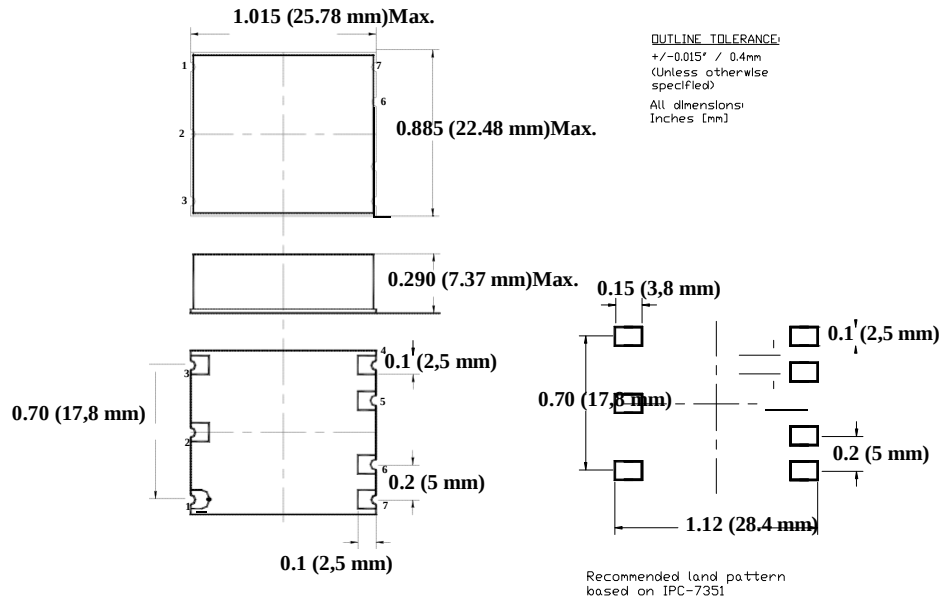
Features

- **Small, Low Profile SMD Package**
- **Very Low Phase Jitter and Phase Noise**
- **Excellent Frequency Stability**
- **Ultra High Frequency – up to 2.5 GHz**
- **CMOS, Sine-Wave, Differential PECL or LVDS outputs available**
- **Military/Space**

Part Numbering Example: CTXWFS1DVM - XX.XXXX M

CTXW	F	S	17	D	V	M	XX.XXXXM
SERIES	VOLTAGE	OUTPUT	STABILITY	OPERATING TEMP.	VOLTAGE CONTROL	GRADE	FREQUENCY
	0= 5.0V A= 3.3V	C=CMOSL P=PECL L=LVDS S=Sinemave	3 = ± 0.28 ppm 2 = ± 2.5 ppm 1 = ± 1.0 ppm	E = 0 °C to 60 °C B = -20 °C to 70 °C C = -30 °C to 70 °C D = -40 °C to 85 °C	V=W/V.Control N=No V.Control	N = Industrial Std M=MIL-STD-883B B= MIL-PFR-55310D	30 ~2500.000 MHz

Note: Vc is not available with Code 3 Stability



Note: For frequency stability over temperature ± 1 ppm and tighter, the package height may be 10mm or 12.5mm

Electrical Connections

Pin Out	Pin #1- Voltage Control ; Pin #2 – N/C ; Pin #3 – Vcc; Pin#4 – Output, CMOS, or Sine; Pin #5 – PECL/LVDS Output; Pin #6 – PECL/LVDS Complementary Output; Pin #7 - GND
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Specifications

Parameter	Symb	Condition	Min	Typ	Max	Unit	Note
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Electrical

Frequency Range	F	CMOS LVDS PECL, Sine-wave	30 30 30		200 1,000 2,500	MHz	
Input Voltage	Vcc		3.135 4.75	3.30 5.0	3.465 5.25	V	A 0
Input Current	Icc	CMOS, Sine PECL, Sine, LVDS			30 100	mA	@100MHz, 3.3V @622MHz, 3.3V
Frequency Stab.	$\Delta F/F$	Overall, available			± 4.6		20 years
Frequency Stability	$\Delta F/F$	vs. Temperature vs. Vcc aging		± 0.5 ± 0.1 ± 1 ± 3.5	± 1	ppm ppm/V ppm/year ppm	See chart First Year 10 years
Calibration	$\Delta F/F$	As shipped, 25 °C		± 0.5	± 1	ppm	
Load		CMOS Sine PECL LVDS	15pf/10K Ohm Internally AC-coupled 50 Ohm 50 Ohm to Vcc-2V or Thevenin equivalent 100 Ohm between the outputs receiving end				
Duty cycle		@50%	45	50	55	%	CMOS, PECL, LVDS
Rise/Fall time	Tr/Tf	20 to 80 %		3 0.35		Ns	CMOS PECL, LVDS
Logic "1" level	Voh	CMOS	0.9Vcc			V	
Logic "0" level	Vol	CMOS			0.1Vcc	V	
Logic "1" level	Voh	PECL	Vcc-0.96		Vcc-0.81	V	100K available
Logic "0" level	Vol	PECL	Vcc-1.85		Vcc-1.65	V	100K available
Output Levels, LVDS	Vod	Differential Amplitude	247	330	454	mV	
		Amplitude error			50	mV	
	Vof	Offset Voltage	1.125	1.25	1.375	V	
		Offset Voltage Error			50	mV	
Output power	P	Sine-wave Into 50 Ohm	0 4	3 7		dBm	3.3V 5.0V
Start up time	Ts			2	10	ms	
Phase Jitter		1 σ		0.4 0.2	1 0.4	ps	100Hz to 20MHz 12KHz to 20MHz
Subharmonics		PECL, LVDS, Sine PECL, Sine CMOS, Sine		-45 -40	-40 -35 None	dBc	F>250MHz F>1,000MHz F<250MHz
Spurious					-60	dBc	
Harmonics		Sine-wave		-30	-25 -15	dBc	F<1,000MHz F $\geq$ 1,000MHz
SSB Phase Noise		@10Hz @100 Hz @1 KHz @10 KHz @100 KHz		-80 -110 -140 -155 -160		dBc/Hz	@100MHz
SSB Phase Noise		@10Hz @100 Hz @1 KHz @10 KHz @100 KHz		-60/-60 -90/-90 -120/-120 -140/-145 -145/-150		dBc/Hz	@622MHz; PECL, LVDS/Sine
SSB Phase Noise		@10Hz @100 Hz @1 KHz @10 KHz @100 KHz		-60 -90 -120 -130 -135		dBc/Hz	@1,000MHz

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Electrical (continued)

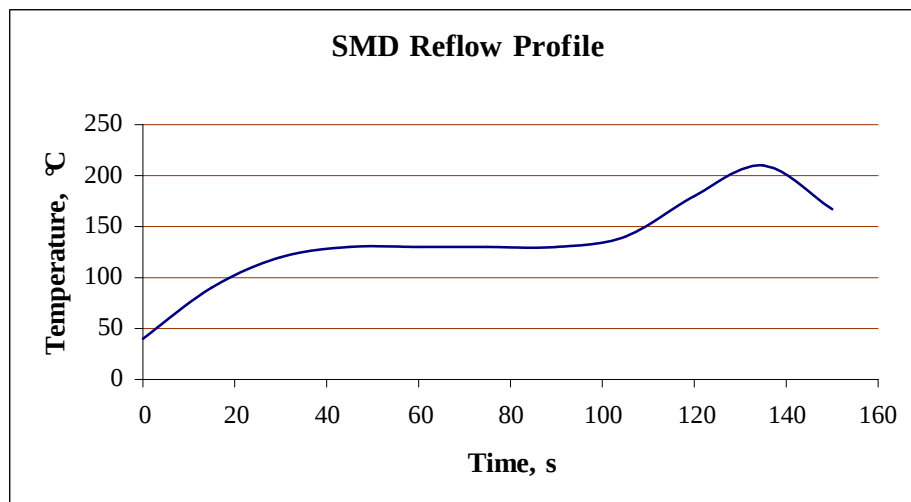
Parameter	Symb	Condition	Min	Typ	Max	Unit	Note
Input Impedance			> 10KOhm				
Control voltage	V _c		0		3.3	V	
Modulation bandwidth	MB		2 Hz				Contact Factory for wider MB
Deviation		V _c =0V to 3.3V, 25 °C	±5	±7		ppm	

Absolute Maximum Ratings

Parameter	Symb	Condition	Min	Typ	Max	Unit	Note
Input Break Down Voltage	V _{cc}		-0.5		5.5	V	
Storage temp.	T _s		-40		105	°C	
Contr. Voltage	V _c		-1		9	V	

Environmental and Mechanical

Operating temp. range	0 °C to 70 °C , -40 °C to 85 °C, see chart, page 1					
Mechanical Shock	Per MIL-STD-202, Method 213, Cond. E					
Thermal Shock	Per MIL-STD-883, Method 1011, Cond. A					
Vibration	Per MIL-STD-883, Method 2007, Cond. A					
Soldering Conditions	See MAX reflow profile; The device may be reflowed once. Reflowing upside down is not allowed. NO CLEAN assembly is recommended.					
Hermetic Seal	Leak rate less than 1x10 ⁻⁸ atm.cc/s of helium (crystal only)					

Maximum solder reflow profile

The device may be reflowed once. Reflowing upside down is not allowed. NO CLEAN assembly is recommended.